TOSHIBA Transistor Silicon NPN Epitaxial Type

## 2SC5030

# Strobe Flash Applications Medium Power Amplifier Applications

• High DC current gain:  $h_{FE}$  (1) = 800 to 3200 ( $V_{CE}$  = 2 V,  $I_{C}$  = 0.5 A) :  $h_{FE}$  (2) = 250 (min) ( $V_{CE}$  = 2 V,  $I_{C}$  = 4 A)

• Low saturation voltage:  $V_{CE (sat)} = 0.5 \text{ V (max)}$  ( $I_{C} = 4 \text{ A}, I_{B} = 40 \text{ mA}$ )

• High collector power dissipation: PC = 1.3 W

#### **Maximum Ratings (Ta = 25°C)**

Characteristics Sy		mbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	50	V	
Collector-emitter voltage		V <sub>CES</sub>	40	V	
		V <sub>CEO</sub> 20			
Emitter-base voltage		$V_{EBO}$	8	>	
Collector current	DC I	С	5	A	
	Pulse (Note)	I <sub>CP</sub>	8		
Base current		ΙΒ	0.5	Α	
Collector power dissipation		P <sub>C</sub> 1.	3	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	

Unit: mm

8.0±0.2

1.4±0.1

1.05±0.1

0.5-0.05

1.2 3

1. EMITTER
2. COLLECTOR
3. BASE

JEDEC

JEITA

TOSHIBA 2
8M1A

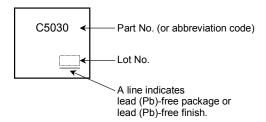
Weight: 0.55 g (typ.)

Note: Conditions: Pulse width = 10 ms (max), duty cycle = 30% (max)

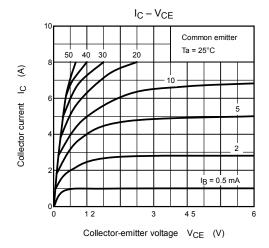
#### **Electrical Characteristics (Ta = 25°C)**

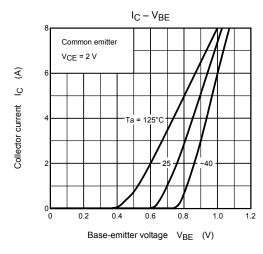
Characteristics Sy	mbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0	_	— 10	0	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 8 V, I <sub>C</sub> = 0	_	— 10	0	nA
Collector-emitter breakdown voltage	V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	20	_	_ V	
DC current gain	h <sub>FE (1)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	800	— 32	00	
	h <sub>FE (2)</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 4 A	250	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 4 A, I <sub>B</sub> = 40 mA	_	<b>—</b> 0.	5	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 4 A	_	<b>—</b> 1.	2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.5 A	— 15	D	— MI	l z
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	<b>—</b> 45		— pF	

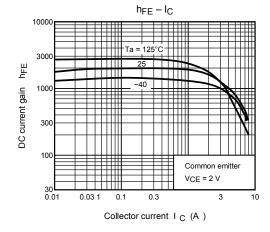
### Marking

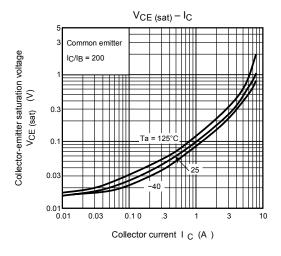


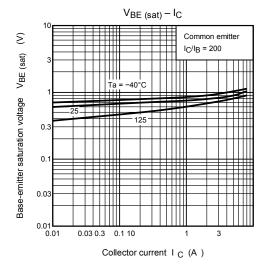
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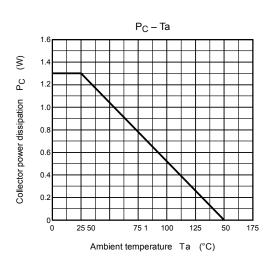




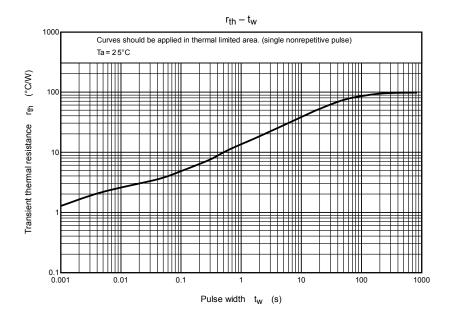


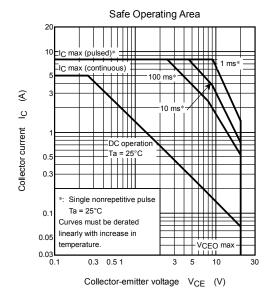






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